

DESCRIPTION

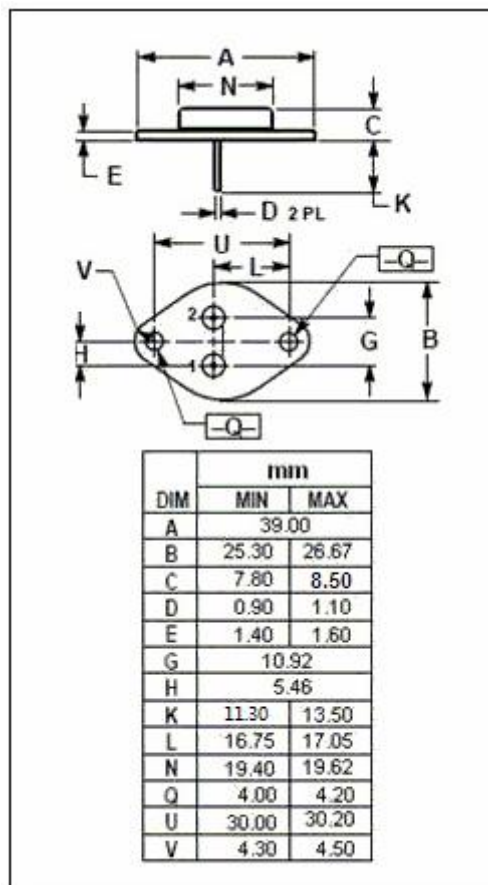
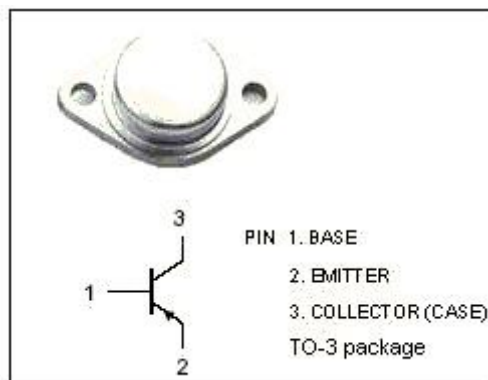
- High Power Dissipation-
: $P_C = 100\text{W}(\text{Max.})@T_C=25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120\text{V}(\text{Min.})$
- Complement to Type 2SC1116

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-10	A
I_B	Base Current-Continuous	-4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	100	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SA747****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA ; I _B = 0	-120			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -0.5A			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -6V; I _C = 0			-1.0	mA
h _{FE}	DC Current Gain	I _C = -3A; V _{CE} = -4V	30			
f _T	Current-Gain—Bandwidth Product	I _E = 0.5A; V _{CE} = -12V		15		MHz

Switching times

t _r	Rise Time	I _C = -3A , R _L = 4 Ω , V _{CC} = -12V I _{B1} = -0.2A; I _{B2} = 50mA		1.2		μ s
t _{stg}	Storage Time			3.3		μ s
t _f	Fall Time			0.8		μ s